安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO.，LTD.

DSK22-DSK210

SOD-123FL Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降
High current capability 高电流能力
Surface mount device 表面贴装器件
Case 封装:SOD-123FL

■Maximum Rating 最大额定值

(T$_A$=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

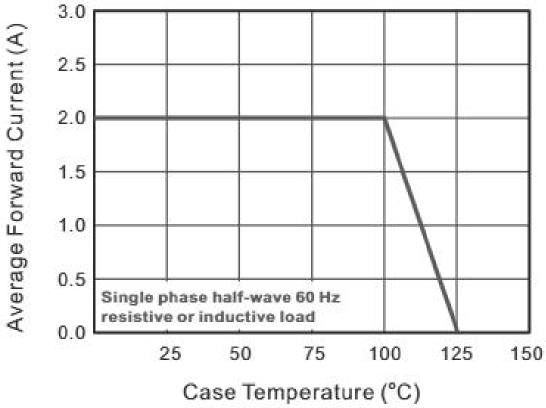
Characteristic 特性参数	Symbol 符号	DSK 22	DSK 23	DSK 24	DSK 25	DSK 26	DSK 27	DSK 28	DSK 29	DSK 210	Unit 单位
Marking 印字		K22	K23	K24	K25	K26	K27	K28	K29	K210	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	20	30	40	50	60	70	80	90	100	V
DC Reverse Voltage 直流反向电压	V_R	20	30	40	50	60	70	80	90	100	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	14	21	28	35	42	49	56	63	70	V
Forward Rectified Current 正向整流电流	I_F	2									A
Peak Surge Current 峰值浪涌电流	I_{FSM}	50									A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	85									℃/W
Junction/Storage Temperature 结温/储藏温度	T_J,T_{stg}	-50to+150℃									℃

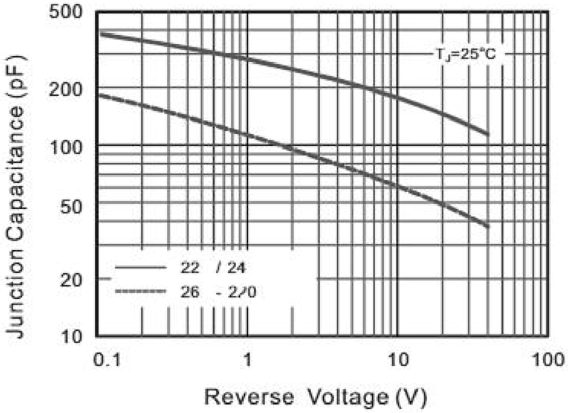
■Electrical Characteristics 电特性

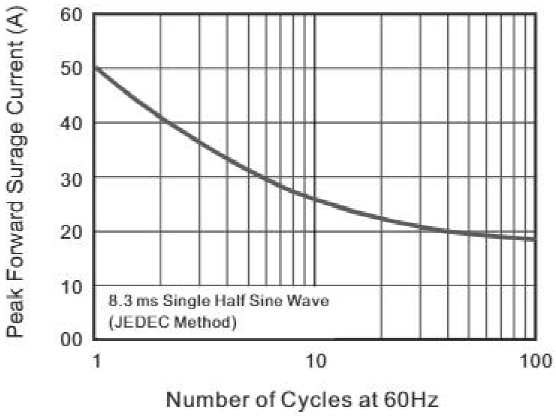
(T$_A$=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

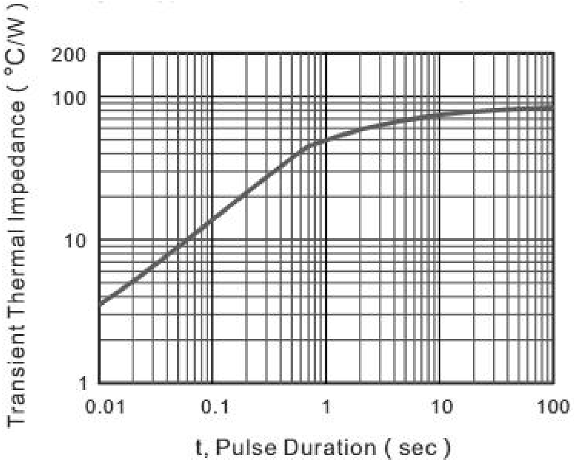
Characteristic 特性参数	Symbol 符号	DSK22-DSK25	DSK26-DSK27	DSK28-DSK210	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.55	0.70	0.85	V	I_F=2A
Reverse Current 反向电流	I_R(25℃) (100℃)	0.5 5		0.3 3	mA	V_R=V_{RRM}
Diode Capacitance 二极管电容	C_D	220	80		pF	V_R=4V, f=1MHz

■Typical Characteristic Curve 典型特性曲线









■SOD-123FL Dimension 外形封装尺寸 Unit in millimeters 单位：毫米